

BAV199W

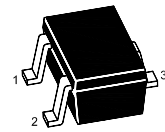
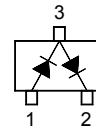
Silicon Epitaxial Planar Diode

Low leakage switching double diode

For low leakage current applications

Feature

- Very low leakage current
- Medium speed switching times
- Series pair configuration



SOT-323 Plastic Package

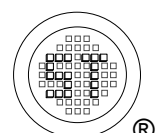
Marking Code: **JY**

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	85	V
Continuous Forward Current	I_F	160	mA
Single Diode		140	
Double Diode			
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
at $t = 1\ \mu\text{s}$		1	
at $t = 1\ \text{ms}$		0.5	
at $t = 1\ \text{s}$			
Power Dissipation	P_d	250	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	85	-	V
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	-	0.9	V
		-	1	
		-	1.1	
		-	1.25	
Reverse Current at $V_R = 75\ \text{V}$ at $V_R = 75\ \text{V}, T_j = 150^\circ\text{C}$	I_R	-	5	nA
		-	80	
Total Capacitance at $V_R = 0, f = 1\ \text{MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_F = I_R = 10\ \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100\ \Omega$	t_{rr}	-	3	μs



Dated : 15/06/2009

